



《风光欣》技术资料

D468

NPN EPITAXIAL SILICON TRANSISTOR

* Collector Current $I_{cm} = 1.5A$

* Emitter-Collector-Base (ECB)

ABSOLUTE MAXIMUM RATINGS($T_A=25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	25	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter -Base Voltage	V_{EBO}	5	V
Collector Current	I_c	1	A
Collector Dissipation	P_c	0.9	W
Junction Temperature	T_J	150	
Storage Temperature	T_{STG}	-55 ~150	

TO-92L



1. Emitter
2. Collector
3. Base

ELECTRICAL CHARACTERISTICS ($T_A=25$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_c=100 \mu A$ $I_E=0$	25			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_c=2mA$ $I_B=0$	20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-100 \mu A$ $I_c=0$	5			V
Collector Cut-off Current	I_{CB0}	$V_{CB}=35V$ $I_E=0$			100	nA
Emitter Cut-off Current	I_{EB0}	$V_{EB}=6V$ $I_E=0$			100	nA
DC Current Gain	H_{FE1}	$V_{CE}=1V$ $I_c=5mA$	45	170		
	H_{FE2}	$V_{CE}=2V$ $I_c=500mA$	85	160	300	
	H_{FE3}	$V_{CE}=1V$ $I_c=800mA$	40	80		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c=800mA$ $I_B=80mA$		0.28	0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c=800mA$ $I_B=80mA$		0.98	1.2	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=1V$ $I_c=10mA$		0.66	1.0	V
Output Capacitance (F=1MHz)	C_{OB}	$V_{CB}=10V$ $I_E=0$		22		pF
Current Gain-Bandwidth Product	f_T	$V_{CE}=10V$ $I_c=50mA$		100	200	MHz

$H_{FE} 2$: CLASSIFICATION

Classification	A	B	C
H_{FE}	100-200	160-320	200-400